2/24/4

PTO/SB/08A (08-03)

Approved for use through 07/31/2006. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE Under the Paperwork Reduction Action of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO						Appli	cation Nun	nber	Filed Herewith			
						Filing	Date		February 24, 2004			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT						First	Named Inve	entor:	Chee-Wee Liu			
(Use as many sheets as necessary)						Exam	iner name:	unknown	GROUP: unknown			
Sheet	1 of 1			Attorney Docket Number			D&F-040					
U.S. PATENT DOCUMENTS												
Examiner Initials*	Cited No. 1		<u>Docum</u> mber - K	Document Number  nber - Kind Code 2/1/ known)					Patentee or Pages, Columns, Lines Cited Document Where Relevant Passages or Figures Appear			
		US-										
		US-										
FOREIGN PATENT DOCUMENTS												
Examiner Initials*	No. Service Patent Document  Cutry Code Number Kind Code Of Of Interview Code					F	Publication Date MM-DD- YYYY	Name of F Applican	Patentee or t of Cited	Pages, Columns, Lines Where Relevant Passages or Figures Appear	Té	
	·											
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)												
€0	G. Kastner and Gosele, "Principles Of Strain Relaxation In Heteroepitaxial Films Growing On Compliant Substrate", J. Appl. Phys., Vol. 88, pp. 4048-4055, 2000.											
ΕO	F. M. Bufler et al., "Hole and Electron Transport In Strained Si: Orthorhombic Versus Biaxial Tensile Strain", Appl. Phys. Lett., Vol. 81, pp. 82-84, 2002.											
EO	F. M. Bufler, "Hole Transport In Orthorhombically Strained Si", Journal Of Computational Electronics, Vol. 1, pp. 175-177, 2002.											
EO	Xin Wang et al., "Monte Carlo Simulation Of Electron Transport In Simple Orthorhombically Strained Silicon", J. Appl. Phys., Vol. 88, pp. 4717-4724, 2000.											
ΕO	M. V. Fischetti, F. Gamiz, and W. Hansch, "On The Enhanced Electron Mobility In Strained-Silicon Inversion Layers", Journal of Applied Physics, Vol. 92, pp. 7320-7324, 2002.											
EXAMINER SIGNATURE: OLIQUID (1) DATE CONSIDERED: (2/10/04												

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with NPEP 609. Draw line through citation if not in conformance and not considered, include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional). 2 See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. 3 Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). 4 For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. 5kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. 6 Applicant is to place a check mark here if English language Translation is attached.

is attached.

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450. If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2. "EXAMINER: Initial if reference considered, whether or not clation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional). 2 See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. 3 Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). 4 For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. 5Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. 6 Applicant is to place a check mark here if English language Translation is attached.